

[METHOD FOR FORMING AN OXIDE/ NI- TRIDE/OXIDE STACKED LAYER]

Abstract

A method for fabricating a silicon oxide/silicon nitride/silicon oxide stacked layer structure is described. A bottom oxide layer is formed over a substrate. A surface treatment is then performed on the first silicon oxide layer to form an interface layer over the bottom oxide layer. The surface treatment is conducted in a nitrogen ambient. Thereafter, a silicon nitride layer is formed over the interface layer, followed by forming an upper silicon oxide layer over the silicon nitride layer.